Chao-Ching (Chester) Chiang

Address: 3009 SW Archer Rd Apt A2, Gainesville, FL 32608 Phone: 352-328-5477 | E-mail: cchiang@ufl.edu

EDUCATION

University of FloridaGainesville, FloridaPh.D. in Chemical Engineering01/2022-05/2025M.S. in Chemical Engineering08/2021-07/2023

National Taiwan UniversityTaipei, TaiwanB.S. in Chemical Engineering09/2011-01/2016

AWARDS

ECS Bruce Deal & Andy Grove Young Author Award

2023

PATENTS

Fabrication of TiO₂ Nanotube Arrays by Progressive Anodization of Ti Thin Film on Insulated Substrates Inventor: **Chiang**, Esquivel-Upshaw, Ren Application No. US63/690,901 09/05/2024

PUBLICATIONS

Journal Articles <u>Google Scholar</u>

[1] Effect of Substrate Thinning on Temperature Rise in Ga₂O₃ Rectifiers, ECS Journal of Solid State Science and Technology, 2024, CC Chiang, JS Li, HH Wan, F Ren, and SJ Pearton

- [2] Achievement of Low Turn-on Voltage in Ga₂O₃ Schottky and Heterojunction Hybrid Rectifiers Using W/Au Anode Contact, AIP Advances, 2024, CC Chiang, JS Li, HH Wan, F Ren, and SJ Pearton
- [3] Ultra-Low On-Resistance W/β-Ga2O3 Junction Barrier Schottky Rectifiers, ECS Advances, 2024, CC Chiang, JS Li, HH Wan, F Ren, and SJ Pearton
- [4] Effect of Dry Etching to Improve Ohmic Contacts on Bulk, Lightly-Doped β-Ga₂O₃, ECS Journal of Solid State Science and Technology, 2024, CC Chiang, JS Li, HH Wan, F Ren, and SJ Pearton
- [5] The Optimization of NiO Doping, Thickness, and Extension in kV-Class NiO/Ga₂O₃ Vertical Rectifiers, Crystals, 2023, CC Chiang, JS Li, HH Wan, F Ren, and SJ Pearton
- [6] E-mode AlGaN/GaN HEMTs Using p-NiO Gates, Journal of Vacuum Science & Technology B, 2023, CC Chiang, HH Wan, JS Li, F Ren, TJ Yoo, H Kim, and SJ Pearton
- [7] Ion Energy Dependence of Dry Etch Damage Depth in Ga₂O₃ Schottky Rectifiers, Applied Surface Science, 2023, CC Chiang, X Xia, JS Li, F Ren, and SJ Pearton
- [8] Enhancing the Hydrophobicity and Antibacterial Properties of SiCN-Coated Surfaces with Quaternization to Address Peri-Implantitis, Materials, 2023, CC Chiang, X Xia, V Craciun, MG Rocha, SEA Camargo, FRG Rocha, SK Gopalakrishnan, KJ Ziegler, F Ren, and JF Esquivel-Upshaw
- [9] Selective Wet and Dry Etching of NiO over β-Ga₂O₃, ECS Journal of Solid State Science and Technology, 2022, **CC Chiang**, X Xia, JS Li, F Ren, and SJ Pearton
- [10] Evaluation of Dry Stored Disposable Sensor Strip on Rapid SARS-CoV-2 Detection Platform, Journal of Vacuum Science & Technology B, 2023, **CC Chiang**, CW Chiu, F Ren, CT Tsai, YT Liao, JF Esquivel-Upshaw, and SJ Pearton
- [11] Threshold Ion Energies and Cleaning of Etch Residues During Inductively Coupled Etching of NiO/Ga₂O₃ in BCl₃, ECS Journal of Solid State Science and Technology, 2022, **CC Chiang**, X Xia, JS Li, F Ren, and SJ Pearton
- [12] Analytical Specificity and Microbial Interference Study of a 30-Second Quantitative SARS-CoV-2 Detection Biosensor System, ECS Journal of Solid State Science and Technology, 2022, CC Chiang, CW Chiu, F Ren, CT Tsai, YT Liao, JF Esquivel-Upshaw, and SJ Pearton
- [13] Detailed Simulation of Fluid Dynamics and Heat Transfer in Coffee Bean Roaster, Journal of Food Process Engineering, 2017, CC Chiang, DY Wu, and DY Kang
- [14] Relationships between the Solution and Solid-State Properties of Solution-Cast Low-K Silica Thin Films, Physical Chemistry Chemical Physics, 2016, CC Chiang, CY Su, AC Yang, TY Wang, WY Lee, CC Hua, and DY Kang
- [15] Demonstration of 4.7 kV Breakdown Voltage in NiO/β-Ga₂O₃ Vertical Rectifiers, Applied Physics Letters, 2022, JS Li, CC Chiang, X Xia, TJ Yoo, F Ren, H Kim, and SJ Pearton

- [16] Annealing Temperature Dependence of Band Alignment of NiO/β-Ga₂O₃, Journal of Physics D: Applied Physics, 2022, X Xia, JS Li, **CC Chiang**, TJ Yoo, F Ren, H Kim, and SJ Pearton
- [17] Temperature Dependence of On-off Ratio and Reverse Recovery Time in NiO/β-Ga₂O₃ Heterojunction Rectifiers, Journal of Vacuum Science & Technology A, 2022, JS Li, CC Chiang, X Xia, F Ren, and SJ Pearton
- [18] Superior High-temperature Performance of 8 kV NiO/Ga₂O₃ Vertical Heterojunction Rectifiers, Journal of Materials Chemistry C, 2023, JS Li, **CC Chiang**, X Xia, HH Wan, F Ren, and SJ Pearton
- [19] Reproducible NiO/Ga₂O₃ Vertical Rectifiers with Breakdown Voltage > 8 kV, Crystals, 2023, JS Li, HH Wan, CC Chiang, X Xia, TJ Yoo, H Kim, F Ren, and SJ Pearton
- [20] 7.5 kV, 6.2 GW cm⁻² NiO/β-Ga₂O₃ Vertical Rectifiers with On–off Ratio Greater than 10¹³, Journal of Vacuum Science & Technology A, 2023, JS Li, CC Chiang, X Xia, HH Wan, F Ren, and SJ Pearton
- [21] Deposition of Sputtered NiO as a p-type Layer for Heterojunction Diodes with Ga₂O₃, Journal of Vacuum Science & Technology A, 2023, JS Li, X Xia, CC Chiang, DC Hays, BP Gila, V Craciun, F Ren, and SJ Pearton
- [22] Effect of Drift Layer Doping and NiO Parameters in Achieving 8.9 kV Breakdown in 100 μm Diameter and 4 kV/4 A in 1 mm Diameter NiO/β-Ga₂O₃ Rectifiers, Journal of Vacuum Science & Technology A, 2023, JS Li, CC Chiang, X Xia, HH Wan, F Ren, and SJ Pearton
- [23] Thermal Stability of Band Offsets of NiO/GaN, Journal of Vacuum Science & Technology A, 2022, X Xia, JS Li, CC Chiang, TJ Yoo, F Ren, H Kim, and SJ Pearton
- [24] Rapid SARS-CoV-2 Diagnosis Using Disposable Strips and a Metal-oxide-semiconductor Field-effect Transistor Platform, Journal of Vacuum Science & Technology B, 2022, CW Chiu, M Xian, JL Stephany, X Xia, CC Chiang, F Ren, CT Tsai, et al.
- [25] Reversible Total Ionizing Dose Effects in NiO/Ga₂O₃ Heterojunction Rectifiers, Journal of Applied Physics, 2023, JS Li, CC Chiang, X Xia, S Stepanoff, A Haque, DE Wolfe, F Ren, and SJ Pearton
- [26] High Sensitivity CIP2A Detection for Oral Cancer Using a Rapid Transistor-based Biosensor Module, Journal of Vacuum Science & Technology B, 2023, M Xian, JL Stephany, CW Chiu, CC Chiang, F Ren, CT Tsai, SS Shan, et al.
- [27] Dynamic Switching of 1.9 A/1.76 kV Forward Current NiO/β-Ga₂O₃ Rectifiers, ECS Journal of Solid State Science and Technology, 2022, JS Li, CC Chiang, X Xia, CT Tsai, F Ren, YT Liao, and SJ Pearton
- [28] Operation of NiO/β-(Al_{0.21}Ga_{0.79})₂O₃/Ga₂O₃ Heterojunction Lateral Rectifiers at up to 225° C, ECS Journal of Solid State Science and Technology, 2023, HH Wan, JS Li, CC Chiang, X Xia, F Ren, H Masten, JS Lundh, J Spencer, et al.
- [29] Comparison of 10 MeV Neutron Irradiation Effects on NiO/Ga₂O₃ Heterojunction Rectifiers and Ni/Au/Ga₂O₃ Schottky Rectifiers, ECS Journal of Solid State Science and Technology, 2023, JS Li, X Xia, **CC Chiang**, HH Wan, F Ren, J Kim, and SJ Pearton
- [30] Type-II Band Alignment of NiO/α-Ga₂O₃ for Annealing Temperatures up to 600° C, Journal of Vacuum Science & Technology A, 2022, X Xia, JS Li, CC Chiang, TJ Yoo, E Hershkovitz, F Ren, H Kim, J Kim, et al.
- [31] Properties of SiCN Films Relevant to Dental Implant Applications, Materials, 2023, X Xia, CC Chiang, SK Gopalakrishnan, AV Kulkarni, F Ren, KJ Ziegler, and JF Esquivel-Upshaw
- [32]β-Ga₂O₃ Orientation Dependence of Band Offsets with SiO₂ and Al₂O₃, Journal of Vacuum Science & Technology A, 2023, HH Wan, JS Li, **CC Chiang**, X Xia, DC Hays, F Ren, and SJ Pearton
- [33] Impact of Solid-State Charge Injection on Spectral Photoresponse of NiO/Ga₂O₃ PN Heterojunction, *Preprints*, 2023, A Schulte, S Modak, Y Landa, A Atman, JS Li, **CC Chiang**, F Ren, SJ Pearton, and L Chernyak
- [34] Vertical NiO/β-Ga₂O₃ Rectifiers Grown by Metalorganic Chemical Vapor Deposition, Journal of Vacuum Science & Technology A, 2023, HH Wan, JS Li, CC Chiang, F Ren, TJ Yoo, H Kim, A Osinsky, F Alema, and SJ Pearton
- [35] 15 MeV Proton Damage in NiO/β-Ga₂O₃ Vertical Rectifiers, Journal of Physics: Materials, 2023, JS Li, CC Chiang, X Xia, HH Wan, J Kim, F Ren, and SJ Pearton
- [36] 1 mm², 3.6 kV, 4.8 A NiO/Ga₂O₃ Heterojunction Rectifiers, ECS Journal of Solid State Science and Technology, 2023, JS Li, **CC Chiang**, X Xia, HH Wan, F Ren, and SJ Pearton
- [37] Annealing Stability of NiO/Ga₂O₃ Vertical Heterojunction Rectifiers, Crystals, 2023, JS Li, HH Wan, **CC Chiang**, F Ren, and SJ Pearton
- [38] High Sensitivity Saliva-based Biosensor in Detection of Breast Cancer Biomarkers: HER2 and CA15-3, Journal of Vacuum Science & Technology B, 2024, HH Wan, H Zhu, CC Chiang, JS Li, F Ren, CT Tsai, YT Liao, D Neal, JF Esquivel-Upshaw, and SJ Pearton

- [39] Selective and Nonselective Plasma Etching of (Al_{0.18}Ga_{0.82})₂O₃/Ga₂O₃ Heterostructures, Journal of Vacuum Science & Technology A, 2024, HH Wan, **CC Chiang**, JS Li, F Ren, F Alema, A Osinsky, and SJ Pearton
- [40] Breakdown Up to 13.5 kV in NiO/β-Ga₂O₃ Vertical Heterojunction Rectifiers, ECS Journal of Solid State Science and Technology, 2024, JS Li, HH Wan, CC Chiang, TJ Yoo, MH Yu, F Ren, H Kim, YT Liao, and SJ Pearton
- [41] Point-of-Care Detection of HER2 and CA 15-3 in Breast Cancer Patients: Dual-Channel Biosensor Implementation, ECS Journal of Solid State Science and Technology, 2024, HH Wan, H Zhu, CC Chiang, X Xia, JS Li, F Ren, CT Tsai, YT Liao, TC Chou, D Neal, and JF Esquivel-Upshaw
- [42] Sensitive Detection of Oral Leukoplakia: Analyzing P90 Biomarkers in Saliva and Tissue, Biosensors, 2024, HH Wan, H Zhu, CC Chiang, JS Li, F Ren, CT Tsai, YT Liao, D Neal, J Katz, and JF Esquivel-Upshaw
- [43] Forward Bias Annealing of Proton Radiation Damage in NiO/Ga₂O₃ Rectifiers, Physica Scripta, 2024, JS Li, CC Chiang, HH Wan, MAJ Rasel, A Haque, J Kim, F Ren, L Chernyak, and SJ Pearton
- [44] Cathodoluminescence Studies of Electron Injection Effects in p-type Gallium Oxide, AIP Advances, 2024, L Chernyak, A Schulte, JS Li, CC Chiang, F Ren, SJ Pearton, C Sartel, V Sallet, Z Chi, Y Dumont, E Chikoidze, and A Ruzin
- [45] Functionalization Process for Commercial Viability: Oral Leukoplakia Detection Using IL-6 Biomarker, ECS Journal of Solid State Science and Technology, 2024, HH Wan, H Zhu, CC Chiang, X Xia, JS Li, F Ren, CT Tsai, YT Liao, TC Chou, D Neal, J Katz, and JF Esquivel-Upshaw
- [46] Dry and Wet Etching of Single-crystal AlN, Journal of Vacuum Science & Technology A, 2024, HH Wan, CC Chiang, JS Li, NS Al-Mamun, A Haque, F Ren, and SJ Pearton
- [47] Switching of kV-class Ga₂O₃ Heterojunction Vertical Rectifiers, Journal of Vacuum Science & Technology A, 2024, JS Li, **CC Chiang**, HH Wan, MH Yu, YT Lin, YY Yang, F Ren, YT Liao, and SJ Pearton
- [48] Effects of Athermal Carrier Injection on Co-60 Gamma-ray Damage in SiC Merged-PiN Schottky diodes, Journal of Vacuum Science & Technology B, 2024, JS Li, CC Chiang, HH Wan, SP Stepanoff, F Ren, A Haque, D Wolfe, and SJ Pearton
- [49] MeV Proton and Neutron Damage Effects on Deep-ultraviolet Light-emitting Diodes, Journal of Vacuum Science & Technology B, 2024, JS Li, CC Chiang, HH Wan, J Kim, S Barke, P Wass, F Ren, JW Conklin, and SJ Pearton
- [50] Lateral NiO/AlN Heterojunction Rectifiers with Breakdown Voltage > 11 kV, ECS Advances, 2024, HH Wan, JS Li, CC Chiang, MH Rahman, A Haque, F Ren, and SJ Pearton

Conference Proceedings/Abstracts

- [1] E-Mode AlGaN/GaN HEMTs Using p-NiO Gates, ECS Transactions, 2024, CC Chiang, HH Wan, JS Li, F Ren, TJ Yoo, H Kim, and SJ Pearton
- [2] Investigation of Quaternized SiCN Thin Film with Enhanced Hydrophobicity and Antibacterial Features for Dental Implants, **CC Chiang**, H Chou, X Xia, F Ren, and JF Esquivel-Upshaw
- [3] Selective Wet and Dry Etching of NiO over β-Ga₂O₃, ECS Transactions, 2023, CC Chiang, X Xia, JS Li, F Ren, and SJ Pearton
- [4] 30-Seconds SARS-CoV-2 Human Sample Diagnosis and Analytical Specificity Analysis Using Disposable Strips on a Metal-Oxide-Semiconductor Field-Effect Transistor Platform, ECS 242, 2022, CC Chiang, CW Chiu, M Xian, F Ren, CT Tsai, YT Liao, JF Esquivel-Upshaw, and SJ Pearton
- [5] Ionization Thresholds and Residue Removal in Inductively Coupled Etching of NiO/Ga₂O₃ with Ar and BCl₃, CS ManTech, 2023, CC Chiang, X Xia, JS Li, F Ren, and SJ Pearton
- [6] Analytical Specificity Study of SARS-CoV-2 Virus Detection with Biosensing Semiconductor-based System, FLAVS, 2022, CC Chiang, CW Chiu, F Ren, CT Tsai, YT Liao, JF Esquivel-Upshaw, and SJ Pearton
- [7] Fabrication and Device Performance of 2.7 kV/2.5 A NiO/Ga₂O₃ Heterojunction Power Rectifiers, ECS Transactions, 2023, X Xia, JS Li, CC Chiang, F Ren, and SJ Pearton
- [8] NiO/β-(Al_xGa_{1-x})₂O₃/Ga₂O₃ Heterojunction Lateral Rectifiers with Reverse Breakdown Voltage > 7 kV, ECS Transactions, 2023, HH Wan, JS Li, CC Chiang, X Xia, F Ren, H Masten, JS Lundh, J Spencer, F Alema, A Osinsky, AG Jacobs, KD Hobart, MJ Tadjer, and SJ Pearton
- [9] Determination of Type II Band Alignment of NiO/α-Ga₂O₃ For Annealing Temperatures Up To 600° C, ECS Transactions, 2023, X Xia, JS Li, CC Chiang, TJ Yoo, E Hershkovitz, F Ren, H Kim, J Kim, DW Jeon, JH Park, and SJ Pearton,

- [10] 4.7 kV Reverse Breakdown Voltage Ultra-Thin Double-layered NiO/β-Ga₂O₃ P-N Junction Rectifiers, ECS 242, 2022, JS Li, CC Chiang, X Xia, TJ Yoo, F Ren, H Kim, and SJ Pearton
- [11] Analytical Specificity Study of SARS-CoV-2 Virus Detection with Biosensing Semiconductor-Based System, GRACE, 2022, CC Chiang, CW Chiu, F Ren, CT Tsai, YT Liao, JF Esquivel-Upshaw, and SJ Pearton
- [12] Operation up to 225° C of NiO/β-(Al_{0.21}Ga_{0.79})₂O₃/Ga₂O₃ Heterojunction Lateral Rectifiers, ECS Transactions, 2024, HH Wan, JS Li, CC Chiang, X Xia, F Ren, H Masten, JS Lundh, J Spencer, F Alema, A Osinsky, AG Jacobs, KD Hobart, M Tadjer, and SJ Pearton
- [13] Demonstration of Record Breakdown up to 13.5 kV in NiO/β-Ga2O3 Vertical Rectifiers, Device Research Conference, 2024, JS Li, HH Wan, CC Chiang, TJ Yoo, MH Yu, F Ren, H Kim, YT Liao, and SJ Pearton

RESEARCH EXPERIENCES

University of Florida, Ren Research Lab Position: Graduate Research Assistant

Gainesville, Florida 08/2021-Present 08/2021-Present

Position: Ph.D. student (Advisor: Prof. Fan Ren)

- Ultrawide bandgap semiconductor devices
 - -Designed, fabricated, and characterized high-performance β-Ga₂O₃ Schottky diodes, NiO/β-Ga₂O₃ PN junction rectifiers, and NiO-gated GaN HEMTs.
 - -Studied wet and dry etching process refinement of device fabrication.
 - -Excelled in the operation of advanced semiconductor device fabrication and characteristic equipment including photolithography, E-beam evaporator, PECVD, ICP etching, SEM, RIE, etc.
- Semiconductor device finite element simulation
 - -Simulated electrical properties of different designs of NiO/β-Ga₂O₃ PN junction rectifiers
 - -Investigated thermal dissipation solutions on Ga₂O₃ thinned-down substrate devices.
- Biosensor detection platform development
 - -Developed a handheld sensor platform for detecting qualitative results of COVID-19, breast cancer, and oral cancer in saliva.
- Surface coating and modification of dental implants
 - -Modified silicon carbon nitride surface and examined the antibacterial ability for the prevention of peri-implantitis through bacteria and cell culture.